

25.(Currently Amended) *A method of forming a bonded assembly, said method comprising the steps of:*

*positioning an IC chip adjacent to a substrate with a thermosetting adhesive between said IC chip and said substrate to adhere said IC chip to said substrate, said substrate comprising an epoxy resin reinforced with fiberglass;*

*irradiating said substrate with near infrared light toward said IC chip such that some energy of said light is absorbed by said substrate and some energy of said light passes through said substrate to said adhesive to substantially cure said adhesive; and* ~~A method as set forth in claim 22 further comprising the step of~~

*halting the irradiating step after said adhesive is heated to a predetermined, curing temperature, and after the halting step, cooling said assembly to substantially room temperature and applying pressure on said IC chip toward said substrate during substantially the entirety of said cooling step.*

26.(Currently Amended) A method as set forth in claim 25~~2~~ wherein said adhesive is ACF.

27.(Currently Amended) A method as set forth in claim 25~~2~~ further comprising the step of using a quartz infrared halogen lamp to perform the step of irradiating said substrate.

28.(Currently Amended) A method as set forth in claim 25~~2~~ wherein said substrate is FR4 dielectric material, and said IC chip is silicon based.

Claims 29 - 31 Cancelled.

32. (Currently Amended) *A method of forming a bonded assembly, said method comprising the steps of:*

*positioning an IC chip adjacent to a substrate with a thermosetting adhesive between said IC chip and said substrate to adhere said IC chip to said substrate, said substrate comprising an epoxy resin reinforced with fiberglass;*

*irradiating said substrate with near infrared light toward said IC chip such that some energy of said light is absorbed by said substrate and some energy of said light passes through said substrate to said adhesive to at least partially cure said adhesive; and ~~A method as set forth in claim 29 further comprising the step of~~*

*halting the irradiating step after said adhesive is heated to a predetermined, curing temperature, and after the halting step, cooling said assembly to substantially room temperature and applying pressure on said IC chip toward said substrate during substantially the entirety of said cooling step.*

33.(Currently Amended) A method as set forth in claim 329 wherein said adhesive is ACF.

34.(Currently Amended) A method as set forth in claim 329 further comprising the step of using a quartz infrared halogen lamp to perform the step of irradiating said substrate.

35.(Currently Amended) A method as set forth in claim 329 wherein said substrate is FR4 dielectric material, and said IC chip is silicon based.

Claims 36 - 38 Cancelled.

39.( Currently Amended) *A method of forming a bonded assembly, said method comprising the steps of:*

*positioning an IC chip adjacent to a substrate with a thermosetting adhesive between said IC chip and said substrate to adhere said IC chip to said substrate, said substrate comprising an epoxy resin reinforced with fiberglass;*

*irradiating said substrate with near infrared light toward said IC chip such that some of said light is absorbed by said substrate and some of said light passes through said substrate to said adhesive to substantially cure said adhesive; and ~~A method as set forth in claim 36 further comprising the step of~~*

halting the irradiating step after said adhesive is heated to a predetermined, curing temperature, and after the halting step, cooling said assembly to substantially room temperature and applying pressure on said IC chip toward said substrate during substantially the entirety of said cooling step.

40.(Currently Amended) A method as set forth in claim 39~~6~~ wherein said adhesive is ACF.

41.(Currently Amended) A method as set forth in claim 39~~6~~ further comprising the step of using a quartz infrared halogen lamp to perform the step of irradiating said substrate.

~~method as set forth in claim 36 wherein said substrate is FR4 dielectric material, and said IC chip is silicon based.~~